SN54ABT2240A, SN74ABT2240A OCTAL BUFFERS AND LINE/MOS DRIVERS WITH 3-STATE OUTPUTS

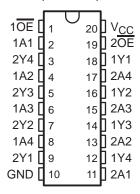
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- Output Ports Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required
- State-of-the-Art EPIC-IIB™ BiCMOS Design Significantly Reduces Power Dissipation
- Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C
- Latch-Up Performance Exceeds 500 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Plastic (N) and Ceramic (J) DIPs, and Ceramic Flat (W) Package

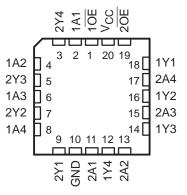
description

These octal buffers and line drivers are designed specifically to improve both the performance and density of 3-state memory address drivers, clock drivers, and bus-oriented receivers and transmitters. Together with the 'ABT2241 and 'ABT2244A, these devices provide combinations of inverting and noninverting outputs, symmetrical active-low output-enable (\overline{OE}) inputs, and complementary OE and \overline{OE} inputs. These devices feature high fan-out and improved fan-in.

SN54ABT2240A . . . J OR W PACKAGE SN74ABT2240A . . . DB, DW, N, OR PW PACKAGE (TOP VIEW)



SN54ABT2240A ... FK PACKAGE (TOP VIEW)



These devices are organized as two 4-bit line drivers with separate \overline{OE} inputs. When \overline{OE} is low, the devices pass inverted data from the A inputs to the Y outputs. When \overline{OE} is high, the outputs are in the high-impedance state.

The outputs, which are designed to sink up to 12 mA, include equivalent 25- Ω series resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54ABT2240A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT2240A is characterized for operation from –40°C to 85°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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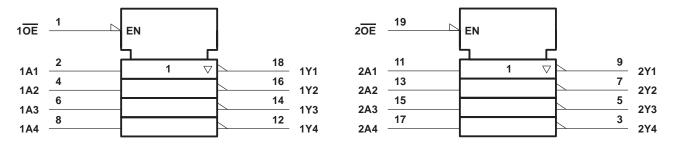


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FUNCTION TABLE (each buffer)

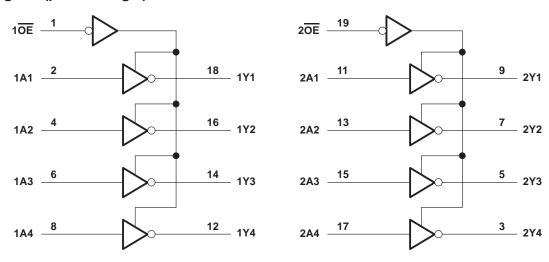
INP	JTS	OUTPUT
OE	Α	Υ
L	Н	L
L	L	Н
Н	Χ	Z

logic symbol†



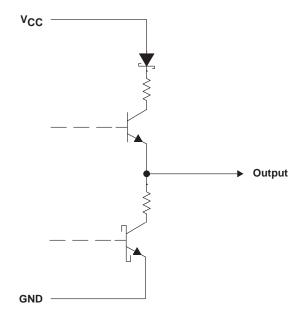
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



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schematic of Y outputs



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	or power-off state, V _O DB package DW package	-0.5 V to 7 V -0.5 V to 5.5 V 30 mA -18 mA -50 mA
Storage temperature range, T _{stg}	. •	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.



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recommended operating conditions (see Note 3)

		SN54ABT	2240A	SN74ABT	UNIT		
			MIN	MAX	MIN	MAX	UNIT
V _{CC} Supply voltage		4.5	5.5	4.5	5.5	V	
V _{IH} High-level input voltage		2		2		V	
V _{IL} Low-level input voltage			0.8		0.8	V	
V _I Input voltage		0	VCC	0	VCC	V	
IOH High-level output current			-24		-32	mA	
IOL Low-level output current			12		12	mA	
Δt/Δν	Input transition rise or fall rate	Outputs enabled		5		5	ns/V
T _A Operating free-air temperature		-55	125	-40	85	°C	

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

DADAA	RAMETER TEST CONDITIONS		NOITIONS	Т	A = 25°C	;	SN54ABT2240A		SN74ABT2240A		UNIT	
PARA	VIETER	l lesi coi	NUTTIONS	MIN	TYP†	MAX	MIN	MAX	MIN	MAX	UNII	
VIK		V _{CC} = 4.5 V,	I _I = -18 mA			-1.2		-1.2		-1.2	V	
V _{CC} = 4.5 V,		$V_{CC} = 4.5 \text{ V},$	$I_{OH} = -3 \text{ mA}$	2.5			2.5		2.5			
\/	V _{CC} = 5 V,		$I_{OH} = -3 \text{ mA}$	3			3		3		V	
VOH		V _{CC} = 4.5 V	I _{OH} = -24 mA	2			2				V	
		VCC = 4.5 V	$I_{OH} = -32 \text{ mA}$	2*					2			
VOL		$V_{CC} = 4.5 \text{ V},$	I _{OL} = 12 mA			0.8		0.8		0.8	V	
V _{hys}					100						mV	
II		$V_{CC} = 5.5 \text{ V},$	$V_I = V_{CC}$ or GND			±1		±1		±1	μΑ	
lozh		V _{CC} = 5.5 V,	V _O = 2.7 V			10*		10		10	μΑ	
lozL		V _{CC} = 5.5 V,	V _O = 0.5 V			-10*		-10		-10	μΑ	
l _{off}		$V_{CC} = 0$,	V_I or $V_O \le 4.5 \text{ V}$			±100				±100	μΑ	
ICEX		V _C C = 5.5 V, V _O = 5.5 V	Outputs high			50		50		50	μА	
I _O ‡		V _{CC} = 5.5 V,	V _O = 2.5 V	-50	-100	-180	-50	-180	-50	-180	mA	
			Outputs high		1	250		250		250	μΑ	
Icc		$V_{CC} = 5.5 \text{ V}, I_{O} = 0,$ $V_{I} = V_{CC} \text{ or GND}$	Outputs low		24	30		30		30	mA	
		V1 = VCC 01 011B	Outputs disabled		0.5	250		250		250	μΑ	
	Data	V _{CC} = 5.5 V, One input at 3.4 V,	Outputs enabled			1.5		1.5		1.5		
ΔICC§	inputs	Other inputs at VCC or GND	Outputs disabled			0.05		0.05		0.05	mA	
	Control inputs	V _{CC} = 5.5 V, One input Other inputs at V _{CC} or				1.5		1.5		1.5		
Ci	•	V _I = 2.5 V or 0.5 V			4						pF	
Со		V _O = 2.5 V or 0.5 V			7						pF	

^{*} On products compliant to MIL-PRF-38535, this parameter does not apply.



[†] All typical values are at $V_{CC} = 5 \text{ V}$.

[‡] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

[§] This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

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switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

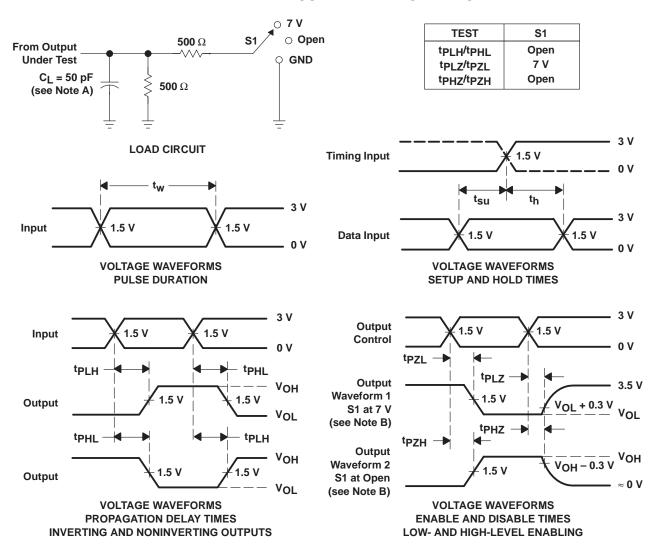
				SN54	4ABT22	40A		
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V ₍	CC = 5 V A = 25°C	', ;	MIN	MAX	UNIT
			MIN	TYP	MAX			
t _{PLH}	А	V	1	3	4	1	5	ns
^t PHL		ı	2.1	4.8	5.8	2.1	6.3	115
^t PZH	ŌĒ		1.5	3.7	4.7	1.5	6.1	ns
t _{PZL}	OE	ı	1.7	6.5	7.6	1.7	8.8	115
^t PHZ	ŌĒ	_	1.8	3.8	6.4	1.5	6.8	ns
^t PLZ	OE .	<u> </u>	1	4.7	5.8	1	6.9	115

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V ₍	CC = 5 V A = 25°C	/, ;	MIN	MAX	UNIT
			MIN	TYP	MAX			
t _{PLH}	۸		1	3	4.1	1	4.8	ns
t _{PHL}	A	ı	2.1	4.1	5.1	2.1	5.4	115
^t PZH	ŌĒ	V	1.1	3.1	4.7	1.1	5.2	ns
t _{PZL}	OE	Ξ , , , , , , , , , , , , , , , , , , ,	1.7	4.5	6.4	1.7	6.8	115
^t PHZ	ŌĒ	V	1.8	3.4	5.7	1.8	6.4	ns
t _{PLZ}	OE	ı	1.9	3.6	6	1.9	6.2	115

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PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{Q} = 50 Ω , $t_{f} \leq$ 2.5 ns, $t_{f} \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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